Sheng-Po Chang

List of Publications by Year
in descending order

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		159585	214800
195	2,967	30	47
papers	citations	h-index	g-index

195	195	195	3495
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer. Applied Physics Letters, 2010, 97, 261103.	3.3	190
2	Hole transport improvement in InGaN/GaN light-emitting diodes by graded-composition multiple quantum barriers. Applied Physics Letters, 2011, 99, .	3.3	123
3	A ZnO nanowire-based humidity sensor. Superlattices and Microstructures, 2010, 47, 772-778.	3.1	118
4	Ultraviolet photodetectors with ZnO nanowires prepared on ZnO:Ga/glass templates. Applied Physics Letters, 2006, 89, 153101.	3.3	101
5	Electroluminescence from n-ZnO nanowires/p-GaN heterostructure light-emitting diodes. Applied Physics Letters, 2009, 95, .	3.3	99
6	Highly Sensitive ZnO Nanowire Acetone Vapor Sensor With Au Adsorption. IEEE Nanotechnology Magazine, 2008, 7, 754-759.	2.0	95
7	Novel fabrication of UV photodetector based on ZnO nanowire/p-GaN heterojunction. Chemical Physics Letters, 2009, 476, 69-72.	2.6	88
8	Efficiency droop alleviation in InGaN/GaN light-emitting diodes by graded-thickness multiple quantum wells. Applied Physics Letters, 2010, 97, .	3.3	76
9	A Lateral ZnO Nanowire Photodetector Prepared on Glass Substrate. Journal of the Electrochemical Society, 2010, 157, K30.	2.9	61
10	ZnO Nanowire-Based Oxygen Gas Sensor. IEEE Sensors Journal, 2009, 9, 485-489.	4.7	58
11	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. ACS Applied Materials & Interfaces, 2017, 9, 14935-14944.	8.0	57
12	High-Performance a-IGZO Thin-Film Transistor Using $ hbox{Ta}_{2}hbox{O}_{5}$ Gate Dielectric. IEEE Electron Device Letters, 2010, , .	3.9	56
13	Fabrication of a White-Light-Emitting Diode by Doping Gallium into ZnO Nanowire on a p-GaN Substrate. Journal of Physical Chemistry C, 2010, 114, 12422-12426.	3.1	54
14	Simple Fabrication Process for 2D ZnO Nanowalls and Their Potential Application as a Methane Sensor. Sensors, 2013, 13, 3941-3950.	3.8	52
15	Solution-Processed UV and Visible Photodetectors Based on Y-Doped ZnO Nanowires with TiO₂ Nanosheets and Au Nanoparticles. ACS Applied Energy Materials, 2018, 1, 2087-2095.	5.1	48
16	A Solar-Blind eta-Ga$_2$O$_3$ Nanowire Photodetector. IEEE Photonics Technology Letters, 2010, 22, 709-711.	2.5	47
17	Electrical and Optical Characteristics of UV Photodetector With Interlaced ZnO Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 990-995.	2.9	45
18	A Visible-Blind TiO2Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	2.9	41

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19	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	4.7	37
20	MBE n-ZnO/MOCVD p-GaN heterojunction light-emitting diode. Thin Solid Films, 2009, 517, 5054-5056.	1.8	36
21	Transparent gas senor and photodetector based on Al doped ZnO nanowires synthesized on glass substrate. Ceramics International, 2017, 43, 5434-5440.	4.8	36
22	Ultraviolet/Visible Photodetectors Based on pâ€“n NiO/ZnO Nanowires Decorated with Pd Nanoparticles. ACS Applied Nano Materials, 2019, 2, 6343-6351.	5.0	36
23	Inserting a p-InGaN layer before the p-AlGaN electron blocking layer suppresses efficiency droop in InGaN-based light-emitting diodes. Applied Physics Letters, 2012, 101, 081120.	3.3	35
24	Sensitivity of EGFET pH Sensors with TiO2 Nanowires. ECS Solid State Letters, 2014, 3, P123-P126.	1.4	35
25	Enhanced field emission of well-aligned ZnO nanowire arrays illuminated by UV. Chemical Physics Letters, 2010, 490, 176-179.	2.6	34
26	Characteristics of efficiency droop in GaN-based light emitting diodes with an insertion layer between the multiple quantum wells and n-GaN layer. Applied Physics Letters, 2010, 97, .	3.3	34
27	Gallium nitride metal-semiconductor-metal photodetectors prepared on silicon substrates. Journal of Applied Physics, 2007, 102, .	2.5	32
28	The synthesis and electrical characterization of Cu₂O/Al:ZnO radial pâ€“n junction nanowire arrays. Nanotechnology, 2009, 20, 365603.	2.6	32
29	ZnO photoconductive sensors epitaxially grown on sapphire substrates. Sensors and Actuators A: Physical, 2007, 140, 60-64.	4.1	31
30	ZnSe Nanowire Photodetector Prepared on Oxidized Silicon Substrate by Molecular-Beam Epitaxy. Journal of the Electrochemical Society, 2009, 156, J73.	2.9	31
31	ZnSe MSM photodetectors prepared on GaAs and ZnSe substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 119, 202-205.	3.5	27
32	Surface HCl treatment in ZnO photoconductive sensors. Thin Solid Films, 2009, 517, 5050-5053.	1.8	25
33	Photoelectrochemical characterization of n-type and p-type thin-film nanocrystalline Cu2ZnSnSe4 photocathodes. Journal of Environmental Chemical Engineering, 2015, 3, 297-303.	6.7	25
34	Highly Stable Ultrathin TiO₂Based Resistive Random Access Memory with Low Operation Voltage. ECS Journal of Solid State Science and Technology, 2018, 7, Q3183-Q3188.	1.8	24
35	A lateral ZnO nanowire UV photodetector prepared on a ZnO:Ga/glass template. Semiconductor Science and Technology, 2009, 24, 075005.	2.0	23
36	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. Materials, 2017, 10, 126.	2.9	23

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37	ZnO-Nanowire-Based Extended-Gate Field-Effect-Transistor pH Sensors Prepared on Glass Substrate. Science of Advanced Materials, 2012, 4, 1174-1178.	0.7	21
38	Homoepitaxial ZnSe MSM photodetectors with various transparent electrodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 127, 164-168.	3.5	20
39	Laterally-grown ZnO-nanowire photodetectors on glass substrate. Superlattices and Microstructures, 2009, 46, 797-802.	3.1	20
40	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. Applied Physics Letters, 2019, 114, .	3.3	20
41	Homoepitaxial ZnSe MIS photodetectors with SiO2 and BST insulator layers. Solid-State Electronics, 2006, 50, 750-753.	1.4	19
42	The Effect of Oxygen Partial Pressure and Annealing Process on the Characteristics of ZnGa₂O₄ÂMSM UV Photodetector. ECS Journal of Solid State Science and Technology, 2019, 8, Q3213-Q3216.	1.8	19
43	Noise Characteristics of ZnO-Nanowire Photodetectors Prepared on ZnO:Ga/Glass Templates. IEEE Sensors Journal, 2007, 7, 1020-1024.	4.7	18
44	Synthesis of CZTSe nanoink via a facile one-pot heating route based on polyetheramine chelation. Solar Energy Materials and Solar Cells, 2014, 128, 156-165.	6.2	18
45	High Responsivity Mg_xZn_{1â^'x}O Film UV Photodetector Grown by RF Sputtering. IEEE Photonics Technology Letters, 2015, 27, 978-981.	2.5	18
46	UV Illumination Room-Temperature ZnO Nanoparticle Ethanol Gas Sensors. ISRN Nanotechnology, 2012, 2012, 1-5.	1.3	18
47	Zinc Oxide Nanoparticle Photodetector. Journal of Nanomaterials, 2012, 2012, 1-5.	2.7	17
48	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ${k}$ Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	2.5	17
49	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	2.2	17
50	AlGaN-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaN last barrier. Applied Physics Letters, 2020, 117, .	3.3	17
51	CuO-Nanowire Field Emitter Prepared on Glass Substrate. IEEE Nanotechnology Magazine, 2011, 10, 1161-1165.	2.0	16
52	Preparation of ZnO Nanoflakes and a Nanowire-Based Photodetector by Localized Oxidation at Low Temperature. Journal of the Electrochemical Society, 2008, 155, K59.	2.9	15
53	Effect of oxygen partial pressure on electrical characteristics of amorphous indium gallium zinc oxide thin-film transistors fabricated by thermal annealing. Vacuum, 2011, 86, 246-249.	3.5	15
54	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. Nanomaterials, 2017, 7, 156.	4.1	15

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55	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. ECS Journal of Solid State Science and Technology, 2019, 8, Q3140-Q3143.	1.8	15
56	Growth of quaternary AlInGaN with various TMI molar rates. Journal of Crystal Growth, 2010, 312, 1920-1924.	1.5	14
57	An investigation of the microstructure, optical and electrical properties of ZITO thin film using the solâ€“gel method. Journal of Sol-Gel Science and Technology, 2010, 54, 347-354.	2.4	14
58	High-Efficiency Si Solar Cell Fabricated by Ion Implantation and Inline Backside Rounding Process. International Journal of Photoenergy, 2012, 2012, 1-7.	2.5	14
59	Investigating the Effect of Piezoelectric Polarization on GaN-Based LEDs With Different Quantum Barrier Thickness. Journal of Display Technology, 2013, 9, 206-211.	1.2	14
60	Two-dimensional ZnO nanowalls for gas sensor and photoelectrochemical applications. Electronic Materials Letters, 2014, 10, 693-697.	2.2	14
61	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga₂O₃ Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	2.9	14
62	The Influence of Different Partial Pressure on the Fabrication of InGaO Ultraviolet Photodetectors. Sensors, 2016, 16, 2145.	3.8	14
63	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	2.6	14
64	AlGaN/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. Semiconductor Science and Technology, 2006, 21, 1064-1068.	2.0	13
65	Crabwise ZnO Nanowire UV Photodetector Prepared on ZnOâ€‰:â€‰Ga/Glass Template. IEEE Nanotechnology Magazine, 2007, 6, 595-600.	2.0	13
66	MBE growth of ZnSe nanowires on oxidized silicon substrate. Superlattices and Microstructures, 2009, 46, 572-577.	3.1	12
67	A study on crystallization, optical and electrical properties of the advanced ZITO thin films using co-sputtering system. Journal of Alloys and Compounds, 2011, 509, 3667-3671.	5.5	12
68	Triple-Junction GaInP/GaAs/Ge Solar Cells With an AZO Transparent Electrode and ZnO Nanowires. IEEE Journal of Photovoltaics, 2013, 3, 991-996.	2.5	12
69	Highly stable ITO/Zn2TiO4/Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	3.6	12
70	ZnO epitaxial layers grown on nitridated Si(100) substrate with HT-GaN/LT-ZnO double buffer. Journal of Crystal Growth, 2008, 310, 290-294.	1.5	11
71	A Quaternary ZnCdSeTe Nanotip Photodetector. Nanoscale Research Letters, 2009, 4, 1540-6.	5.7	11
72	A Deep UV Sensitive ${m Ta}_{2}{m O}_{5}/{m a-IGZO}$ TFT. IEEE Sensors Journal, 2011, 11, 2902-2905.	4.7	11

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73	Growth of ZnSe[sub 1â^'x]Te[sub x] Nanotips and the Fabrication of ZnSe[sub 1â^'x]Te[sub x] Nanotip-Based Photodetector. Journal of the Electrochemical Society, 2010, 157, K1.	2.9	10
74	Influence of Weight Ratio of Poly(4-vinylphenol) Insulator on Electronic Properties of InGaZnO Thin-Film Transistor. Journal of Nanomaterials, 2012, 2012, 1-7.	2.7	10
75	Synthesis of Cu2ZnSnSe4 nanocrystals from metal sources using a facile process in isophorondiamine. Materials Letters, 2013, 98, 71-73.	2.6	10
76	Efficiency of GaN/InGaN double-heterojunction photovoltaic cells under concentrated illumination. Surface and Coatings Technology, 2013, 231, 253-256.	4.8	10
77	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. ECS Journal of Solid State Science and Technology, 2019, 8, Q3034-Q3040.	1.8	10
78	Ambient-Processed, Additive-Assisted CsPbBr3 Perovskite Light-Emitting Diodes with Colloidal NiOx Nanoparticles for Efficient Hole Transporting. Coatings, 2020, 10, 336.	2.6	10
79	Bright CsPbBr3 Perovskite Nanocrystals with Improved Stability by In-Situ Zn-Doping. Nanomaterials, 2022, 12, 759.	4.1	10
80	ZnSe based white light emitting diode on homoepitaxial ZnSe substrate. IET Optoelectronics, 2007, 1, 39-41.	3.3	9
81	Low-frequency noise characteristics of GaN-based UV photodiodes with AlN/GaN buffer layers prepared on Si substrates. Journal of Crystal Growth, 2009, 311, 3003-3006.	1.5	9
82	Characteristics of InGaN-Based Light-Emitting Diodes on Patterned Sapphire Substrates with Various Pattern Heights. Journal of Nanomaterials, 2012, 2012, 1-6.	2.7	9
83	MgZnO/SiO₂/ZnO metalâ€“semiconductorâ€“metal dual-band UVA and UVB photodetector with different MgZnO thicknesses by RF magnetron sputter. Japanese Journal of Applied Physics, 2020, 59, SDDF04.	1.5	9
84	High Stability Flexible Deep-UV Detector Based on All-Oxide Heteroepitaxial Junction. ACS Applied Electronic Materials, 2022, 4, 3099-3106.	4.3	9
85	High-performance amorphous indiumâ€“galliumâ€“zinc oxide thin-film transistors with polymer gate dielectric. Thin Solid Films, 2012, 520, 5455-5458.	1.8	8
86	Fabrication and Photoelectrochemical Behavior of n-Type Cu2ZnSnSe4Thin-Film Electrodes Prepared via Non-Vacuum Nanoinks Process. ECS Journal of Solid State Science and Technology, 2013, 2, Q220-Q223.	1.8	8
87	Beta-Gallium Oxide Nanowire Extended Gate Field Effect Transistor pH Sensors Prepared Using Furnace-Oxidized Gallium Nitride Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 914-917.	0.4	8
88	Investigation of zinc-tin-oxide thin-film transistors with varying SnO2 contents. Electronic Materials Letters, 2014, 10, 89-94.	2.2	8
89	Influence of oxygen on the performance of indium titanium zinc oxide UV sensors fabricated via RF sputtering. Materials Science in Semiconductor Processing, 2018, 74, 297-302.	4.0	8
90	A Novel pH Sensor Using Extended-Gate Field-Effect Transistors with Ga₂O₃ Nanowires Fabricated on SiO₂/Si Template. Science of Advanced Materials, 2015, 7, 475-478.	0.7	8

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91	Low-Frequency Noise Characteristics of Epitaxial ZnO Photoconductive Sensors. Journal of the Electrochemical Society, 2007, 154, J209.	2.9	7
92	Noise Properties of ZnO Nanowalls Deposited Using Rapid Thermal Evaporation Technology. IEEE Photonics Technology Letters, 2013, 25, 213-216.	2.5	7
93	Effect of oxygen vacancy concentration on indium tungsten oxide UV-A photodetector. RSC Advances, 2019, 9, 87-90.	3.6	7
94	Indium Aluminum Zinc Oxide Thin Film Transistor With Al₂O₃ Dielectric for UV Sensing. IEEE Photonics Technology Letters, 2019, 31, 1005-1008.	2.5	7
95	Photoresponses of Zinc Tin Oxide Thin-Film Transistor. Journal of Nanoscience and Nanotechnology, 2020, 20, 1704-1708.	0.9	7
96	Photo-assisted thermally oxidized GaAs insulator layers deposited by photo-CVD. Surface and Coatings Technology, 2006, 200, 3250-3253.	4.8	6
97	Laterally Grown n-ZnO Nanowire/p-GaN Heterojunction Light Emitting Diodes. Journal of the Electrochemical Society, 2010, 157, H866.	2.9	6
98	A Novel Fabrication of pâ€“n Diode Based on ZnO Nanowire/p-NiO Heterojunction. Japanese Journal of Applied Physics, 2011, 50, 01AJ05.	1.5	6
99	InGaN-Based Light-Emitting Diodes With an AlGaN Staircase Electron Blocking Layer. IEEE Photonics Technology Letters, 2012, 24, 1737-1740.	2.5	6
100	Effect of surface modification by self-assembled monolayer on the ZnO film ultraviolet sensor. Applied Physics Letters, 2013, 103, 022101.	3.3	6
101	The inter-metallic oxide of ZnO/ITO/ZnO tri-layer films using a heat-induced diffusion mechanism. Applied Surface Science, 2013, 273, 598-602.	6.1	6
102	Synchrotron radiation based cross-sectional scanning photoelectron microscopy and spectroscopy of n-ZnO:Al/p-GaN:Mg heterojunction. Applied Physics Letters, 2013, 102, .	3.3	6
103	Characterization of High Mg Content MgZnO Ultraviolet Photodetectors with Noise Properties. ECS Journal of Solid State Science and Technology, 2016, 5, Q191-Q194.	1.8	6
104	Bandgap Engineered Ultraviolet Photodetectors with Gallium-Zinc-Oxide via Co-Sputtering Method. ECS Journal of Solid State Science and Technology, 2018, 7, Q3083-Q3088.	1.8	6
105	Voltage-Tunable UVCâ€“UVB Dual-Band Metalâ€“Semiconductorâ€“Metal Photodetector Based on Ga2O3/MgZnO Heterostructure by RF Sputtering. Coatings, 2020, 10, 994.	2.6	6
106	Room temperature photo-CVD SiO2layers on AlGaN and AlGaN/GaN MOS-HFETs. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 404-409.	1.8	5
107	ZnO Nanowire-Based UV Photodetector. Journal of Nanoscience and Nanotechnology, 2010, 10, 1135-1138.	0.9	5
108	Improved Optical and ESD Characteristics for GaN-Based LEDs With an $hbox{n}^{-}hbox{-GaN}$ Layer. IEEE Transactions on Device and Materials Reliability, 2011, 11, 76-80.	2.0	5

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109	Isopropyl Alcohol Sensors of CuO Nanotubes by Thermal Oxidation of Copper Films on Glass. IEEE Sensors Journal, 2011, 11, 3276-3282.	4.7	5
110	Effect of Varied Undoped GaN Thickness on ESD and Optical Properties of GaN-Based LEDs. IEEE Photonics Technology Letters, 2012, 24, 800-802.	2.5	5
111	Growth of ultrathin GaSb layer on GaAs using metalâ€“organic chemical vapor deposition with Sb interfacial treatment. Applied Physics Express, 2016, 9, 095502.	2.4	5
112	Influence of Annealing Ambience on TiO₂Film Ultraviolet Photodetector. ECS Journal of Solid State Science and Technology, 2017, 6, Q3056-Q3060.	1.8	5
113	Fabrication of Zinc Oxide-Based Thin-Film Transistors by Radio Frequency Sputtering for Ultraviolet Sensing Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 3518-3522.	0.9	5
114	Development of Indium Titanium Zinc Oxide Thin Films Used as Sensing Layer in Gas Sensor Applications. Coatings, 2021, 11, 807.	2.6	5
115	10-Gb/s Planar InGaAs P-I-N Photodetectors. IEEE Sensors Journal, 2010, 10, 1559-1563.	4.7	4
116	Effect of Silicon Doped Quantum Barriers on Nitride-Based Light Emitting Diodes. Journal of the Electrochemical Society, 2011, 158, H836.	2.9	4
117	Characteristics of GaN/InGaN Double-Heterostructure Photovoltaic Cells. International Journal of Photoenergy, 2012, 2012, 1-5.	2.5	4
118	Fabrication of ZnO Nanowall-Based Hydrogen Gas Nanosensor. Advanced Materials Research, 2013, 684, 21-25.	0.3	4
119	Performance Enhancement of High-Current-Injected Electrically Programmable Fuse With Compressive-Stress Nitride Layer. IEEE Electron Device Letters, 2014, 35, 297-299.	3.9	4
120	Performance Enhancement of Blue InGaN Light-Emitting Diodes with P-GaN/InGaN SPS Last Barrier and P-AlGaN/GaN SPS EBL. ECS Journal of Solid State Science and Technology, 2016, 5, Q179-Q182.	1.8	4
121	GaN-Based Blue Light-Emitting Diodes with an Electron Transmission Layer. ECS Journal of Solid State Science and Technology, 2017, 6, R154-R157.	1.8	4
122	Suppressing efficiency droop using graded AlGaN/InGaN superlattice electron blocking layer for InGaN-based light-emitting diodes. Journal of Crystal Growth, 2017, 468, 562-566.	1.5	4
123	Growth and Crystal Structure Investigation of InAs/GaSb Heterostructure Nanowires on Si Substrate. IEEE Nanotechnology Magazine, 2018, 17, 1151-1158.	2.0	4
124	Investigation of Conductive Mechanism of Amorphous IGO Resistive Random-Access Memory with Different Top Electrode Metal. Coatings, 2020, 10, 504.	2.6	4
125	Stability-Enhanced Resistive Random-Access Memory via Stacked In_xGa_{1â€“x}O by the RF Sputtering Method. ACS Omega, 2021, 6, 10691-10697.	3.5	4
126	AlGaN-Based Deep Ultraviolet Light-Emitting Diodes with Thermally Oxidized Al_xGa_{2â€“x}O₃ Sidewalls. ACS Omega, 2022, 7, 15027-15036.	3.5	4

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127	ITO/Homoepitaxial ZnSe/ITO MSM Sensors With Thermal Annealing. IEEE Sensors Journal, 2006, 6, 945-949.	4.7	3
128	Fabrication of Crack-Free Metal-Semiconductor-Metal Ultraviolet Photodetectors on Si (111) Substrates Based on Novel AlN/AlGaN Buffer Multilayer Scheme. ECS Transactions, 2007, 11, 117-128.	0.5	3
129	High-Performance a-IGZO Thin-Film Transistor with Organic Polymer Dielectric Layer. , 2011, , .		3
130	Optoelectronic Properties of Thermally Evaporated ZnO Films with Nanowalls on Glass Substrates. Applied Physics Express, 2013, 6, 045201.	2.4	3
131	p-Type Quasi-Mono Silicon Solar Cell Fabricated by Ion Implantation. International Journal of Photoenergy, 2013, 2013, 1-8.	2.5	3
132	Fabrication of Simple GaAs Solar Cell by Zn Diffusion Method. Advanced Materials Research, 2013, 684, 312-316.	0.3	3
133	See-Through Si Thin-Film Tandem Solar Cell Module With Hardener. IEEE Journal of Photovoltaics, 2014, 4, 1013-1017.	2.5	3
134	High Responsivity Indium-Zinc-Oxide Ultraviolet Thin-Film Phototransistor. Journal of Nanoscience and Nanotechnology, 2017, 17, 4864-4866.	0.9	3
135	Amorphous Indium Titanium Zinc Oxide Thin Film Transistor and Impact of Gate Dielectrics on Its Photo-Electrical Properties. ECS Journal of Solid State Science and Technology, 2018, 7, Q3049-Q3053.	1.8	3
136	Bandgap-Engineered Zinc-Tin-Oxide Thin Films for Ultraviolet Sensors. Journal of Nanoscience and Nanotechnology, 2018, 18, 4930-4934.	0.9	3
137	Communicationâ€"Diffusion Break-Assisted Programming Mode for Active Electrically Programmable Fuse. ECS Journal of Solid State Science and Technology, 2018, 7, Q109-Q111.	1.8	3
138	Doping Nitrogen in InGaZnO Thin Film Transistor with Double Layer Channel Structure. Journal of Nanoscience and Nanotechnology, 2018, 18, 2493-2497.	0.9	3
139	Investigation of nitrogen doping effects on light-induced oxygen vacancy ionization and oxygen desorption in c-IGO TFTs. Materials Research Express, 2019, 6, 106445.	1.6	3
140	Indium Aluminum Zinc Oxide Phototransistor With HfO2 Dielectric Layer Through Atomic Layer Deposition. IEEE Sensors Journal, 2020, 20, 1838-1842.	4.7	3
141	Polycrystalline Inâ€"Gaâ€"O Thin-Film Transistors Coupled With a Nitrogen Doping Technique for High-Performance UV Detectors. IEEE Transactions on Electron Devices, 2020, 67, 140-145.	3.0	3
142	Fabrication and Characterization of In0.9Ga0.1O EGFET pH Sensors. Coatings, 2021, 11, 929.	2.6	3
143	Deep Ultraviolet AlGaN-Based Light-Emitting Diodes with p-AlGaN/AlGaN Superlattice Hole Injection Structures. Processes, 2021, 9, 1727.	2.8	3
144	Optical and Electrical Characteristics of ZnO Films Grown on Nitridated Si (1 0 0) Substrate with GaN and ZnO Double Buffer Layers. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1058-1063.	2.9	2

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145	ZnO nanowire-based oxygen gas sensor. , 2008, , .		2
146	Quaternary ZnCdSeTe Nanowires. Journal of Nanoscience and Nanotechnology, 2010, 10, 798-802.	0.9	2
147	Growth and Photoelectric Properties of Twinned ZnSe$_{m {1-x}}$Te$_{m x}$ Nanotips. IEEE Nanotechnology Magazine, 2011, 10, 379-384.	2.0	2
148	Use of the Thermal Chemical Vapor Deposition to Fabricate Light-Emitting Diodes Based on ZnO Nanowire/p-GaN Heterojunction. Journal of Nanomaterials, 2011, 2011, 1-4.	2.7	2
149	Room-Temperature ZnO Nanoparticle Ethanol Gas Sensors under UV Illumination. Advanced Materials Research, 0, 486, 39-43.	0.3	2
150	Amorphous Hafnium-Indium-Zinc Oxide Semiconductor Thin Film Transistors. Journal of Nanomaterials, 2012, 2012, 1-4.	2.7	2
151	Reducing the Current Crowding Effect on Nitride-Based Light-Emitting Diodes Using Modulated P-Extension Electrode Thickness. Japanese Journal of Applied Physics, 2013, 52, 01AG05.	1.5	2
152	Optical Switch of a-IGZO TFT and Triple Junction Photovoltaic Cell. ECS Journal of Solid State Science and Technology, 2017, 6, Q120-Q122.	1.8	2
153	Optical and photo-electrical properties of zinc tin oxide thin-film phototransistor. , 2018, , .		2
154	An Amorphous (Al0.12Ga0.88)2O3 Deep Ultraviolet Photodetector. IEEE Photonics Journal, 2020, 12, 1-8.	2.0	2
155	The Characteristics of Aluminum-Gallium-Zinc-Oxide Ultraviolet Phototransistors by Co-Sputtering Method. Electronics (Switzerland), 2021, 10, 631.	3.1	2
156	Tri-Layer Structure ZnGa2O4-Based Resistive Random Access Memory. ECS Journal of Solid State Science and Technology, 0, , .	1.8	2
157	Investigation of MgIn2O4 MSM UV Photodetector With Different Oxygen Flow Ratios and Post-Annealing Temperatures. ECS Journal of Solid State Science and Technology, 2021, 10, 055014.	1.8	2
158	Performance Improvement of Co-Sputtering AlGaZnO Solar-Blind Photodetectors. IEEE Sensors Journal, 2021, 21, 18682-18687.	4.7	2
159	Growth of InN Nanorods on Glass Substrates by Molecular Beam Heteroepitaxy. Science of Advanced Materials, 2013, 5, 873-880.	0.7	2
160	The characteristics of transparent metal-ZnO contacts and ZnO-based photodiodes. , 2007, 6474, 192.		1
161	GaN photodetectors prepared on silicon and sapphire substrates. , 2008, , .		1
162	Method for Improving the Stability of Gen 5 Silicon Thin-film Tandem Solar Cell. IEEE Journal of Photovoltaics, 2013, 3, 1140-1143.	2.5	1

#	Article	IF	Citations
163	Electrical Properties of Amorphous Zinc-Indium-Tin Oxide Semiconductor Thin-Film Transistors. Nanoscience and Nanotechnology Letters, 2014, 6, 273-278.	0.4	1
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